

Complementary Silicon Plastic Power Transistors

2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- High DC Current Gain
- High Current Gain Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V _{CEO}	30 50 70	Vdc
Collector-Base Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V _{CB}	40 60 80	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current - Continuous	I _C	7.0	Adc
Collector Current - Peak	I _{CM}	10	Adc
Base Current	Ι _Β	3.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

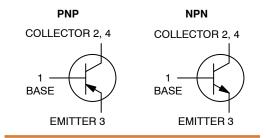
THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

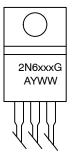
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7 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 30 - 50 - 70 VOLTS, 40 WATTS





MARKING DIAGRAM



2N6xxx = Specific Device Code xxx = See Table on Page 4 G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 4 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 4.

^{1.} Indicates JEDEC Registered Data.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	L		1	1
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 100 mAdc, I _B = 0) 2N6111, 2N6288 2N6109 2N6107, 2N6292	V _{CEO(sus)}	30 50 70	- - -	Vdc
Collector Cutoff Current $(V_{CE} = 20 \text{ Vdc}, I_B = 0)$ 2N6111, 2N6288 $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$ 2N6109 $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$ 2N6107, 2N6292	I _{CEO}	-	1.0 1.0 1.0	mAdc
Collector Cutoff Current (V _{CE} = 40 Vdc, V _{EB(off)} = 1.5 Vdc) 2N6111, 2N6288 (V _{CE} = 60 Vdc, V _{EB(off)} = 1.5 Vdc) 2N6109 (V _{CE} = 80 Vdc, V _{EB(off)} = 1.5 Vdc) 2N6107, 2N6292 (V _{CE} = 30 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C)	I _{CEX}		100 100 100	μAdc
2N6111, 2N6288 (V _{CE} = 50 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) 2N6109 (V _{CE} = 70 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) 2N6107, 2N6292		-	2.0 2.0 2.0	mAdc
Emitter Cutoff Current $(V_{BE} = 5.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	1.0	mAdc
ON CHARACTERISTICS (Note 3)	·			
DC Current Gain $ \begin{aligned} &(I_C=2.0 \text{ Adc, V}_{CE}=4.0 \text{ Vdc}) \\ &2N6107, 2N6292 \\ &(I_C=2.5 \text{ Adc, V}_{CE}=4.0 \text{ Vdc}) \\ &2N6109 \\ &(I_C=3.0 \text{ Adc, V}_{CE}=4.0 \text{ Vdc}) \\ &2N6111, 2N6288 \\ &(I_C=7.0 \text{ Adc, V}_{CE}=4.0 \text{ Vdc}) \\ &All \text{ Devices} \end{aligned} $	h _{FE}	30 30 30 2.3	150 150 150 -	-
Collector–Emitter Saturation Voltage ($I_C = 7.0 \text{ Adc}$, $I_B = 3.0 \text{ Adc}$)	V _{CE(sat)}	-	3.5	Vdc
Base-Emitter On Voltage (I _C = 7.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	-	3.0	Vdc
DYNAMIC CHARACTERISTICS			,	
Current Gain – Bandwidth Product (Note 4) ($I_C = 500 \text{ mAdc}$, $V_{CE} = 4.0 \text{ Vdc}$, $f_{test} = 1.0 \text{ MHz}$) 2N6288, 2N6292 2N6107, 2N6109, 2N6111	f _T	4.0 10	- -	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	-	250	pF
Small–Signal Current Gain ($I_C = 0.5$ Adc, $V_{CE} = 4.0$ Vdc, $f = 50$ kHz)	h _{fe}	20	-	-
	I		1	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

^{4.} $f_T = |h_{fe}| \bullet f_{test}$

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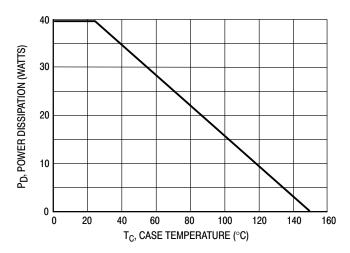
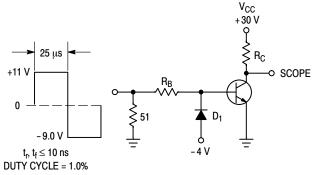


Figure 1. Power Derating



R_B and R_C ARE VARIED TO OBTAIN DESIRED CURRENT LEVELS

D1 MUST BE FAST RECOVERY TYPE, eg: 1N5825 USED ABOVE IB \approx 100 mA MSD6100 USED BELOW IB \approx 100 mA

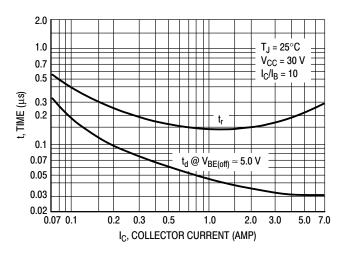
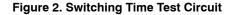


Figure 3. Turn-On Time



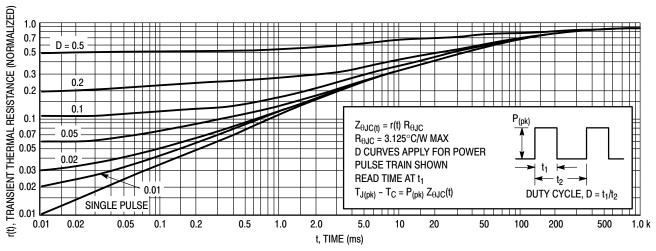


Figure 4. Thermal Response

2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)

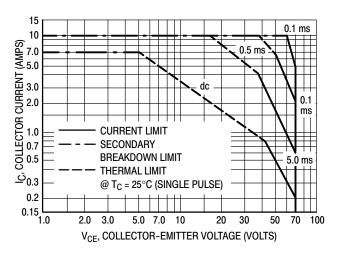


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

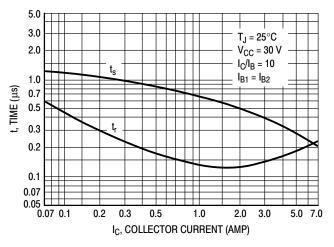


Figure 6. Turn-Off Time

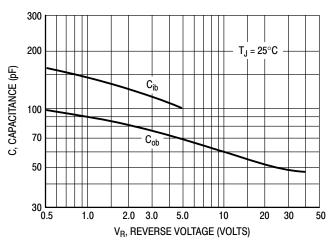


Figure 7. Capacitance

ORDERING INFORMATION

Device	Device Marking	Package	Shipping
2N6292G	2N6292	TO-220 (Pb-Free)	50 Units / Rail

DISCONTINUED (Note 5)

2N6107G	2N6107	TO-220 (Pb-Free)	50 Units / Rail
2N6109G	2N6109	TO-220 (Pb-Free)	50 Units / Rail
2N6111G	2N6111	TO-220 (Pb-Free)	50 Units / Rail
2N6288G	2N6288	TO-220 (Pb-Free)	50 Units / Rail

^{5.} **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

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